

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Tetsuya Taki

Serial No.: Not Yet Assigned

Group Art Unit: Not Yet Assigned

Filing Date: Concurrently Herewith

Examiner: Unknown

For: METHOD FOR PRODUCING P-TYPE GROUP III NITRIDE COMPOUND
SEMICONDUCTOR

Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to Applicants' duty of disclosure under 37 CFR §1.56, Applicant respectfully brings the following documents listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed documents are provided herewith for the convenience of the Examiner. In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3), the relevance of these documents is discussed on pages 2 and 3 of the subject application. Further, English-language Abstracts are attached to some the references.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Date:

9/22/03

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Respectfully submitted,



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INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

T36-160821M/KOH

Application Number

Not Yet Assigned

Applicant(s)

Tetsuya Taki

Filing Date

Concurrently Herewith

Group Art Unit

Unknown

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|-----|-----------------|------------|------------------|-------|----------|-------------------------------|
| | | 5,306,662 | 04/26/1994 | Nakamura, et al. | | | |
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FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
|--|-----|-----------------|------------|---------|-------|----------|-------------|----|
| | | | | | | | YES | NO |
| | | 05-183189 | 07/23/1993 | Japan | | | ABS | |
| | | 05-198841 | 08/06/1993 | Japan | | | ABS | |
| | | 08-097471 | 04/12/1996 | Japan | | | | |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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|--|--|---|
| | | Nakamura, et al., "HOLE COMPENSATION MECHANISM OF P-TYPE GaN FILMS", Jpn. J. App. Phys. Vol. 31 Part 1, No. 5A, May 1992, Pages 1258-1266 |
| | | Amano, et al., "GaN BLUE AND UV LIGHT EMITTING DIODES WITH A PN JUNCTION", Oyo Buturi, Vol. 60, No. 2, 1991, Pages 163-166 |

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.